# LDO Regulator, 100 mA, 18 V, 1 $\mu$ A I<sub>Q</sub>, with PG

# NCV8711

The NCV8711 device is based on unique combination of features – very low quiescent current, fast transient response and high input and output voltage ranges. The NCV8711 is CMOS LDO regulator designed for up to 18 V input voltage and 100 mA output current. Quiescent current of only 1  $\mu$ A makes this device ideal solution for battery– powered, always–on systems. Several fixed output voltage versions are available as well as the adjustable version.

The device (version B) implements power good circuit (PG) which indicates that output voltage is in regulation. This signal could be used for power sequencing or as a microcontroller reset.

Internal short circuit and over temperature protections saves the device against overload conditions.

#### Features

- Operating Input Voltage Range: 2.7 V to 18 V
- Output Voltage: 1.2 V to 17 V
- Capable of Sourcing 140 mA Peak Output Current
- Very Low Quiescent Current: 1 µA typ.
- Low Dropout: 215 mV typ. at 100 mA
- Output Voltage Accuracy ±1%
- Power Good Output (Version B)
- Stable with Small 1 µF Ceramic Capacitors
- Built-in Soft Start Circuit to Suppress Inrush Current
- Over-Current and Thermal Shutdown Protections
- Available in Small TSOP-5 and WDFNW6 (2x2) Packages
- These Devices are Pb-Free and are RoHS Compliant

#### **Typical Applications**

- Body Control Modules
- LED Lighting
- On Board Charger
- General Purpose Automotive



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#### MARKING DIAGRAMS



XXX = Specific Device Code

- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)





XX = Specific Device Code M = Date Code



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 9 of this data sheet.

#### TYPICAL APPLICATION SCHEMATICS



Figure 1. Fixed Output Voltage Application (No PG)







Figure 3. Fixed Output Voltage Application with PG



Figure 4. Adjustable Output Voltage Application with PG

$$V_{OUT} = V_{ADJ} \cdot \left(1 + \frac{R_1}{R_2}\right) + I_{ADJ} \cdot R_1$$

#### SIMPLIFIED BLOCK DIAGRAMS



Note: Blue objects are valid for ADJ version Green objects are valid for FIX version Brown objects are valid for B version (with PG)

Figure 5. Internal Block Diagram

Pin No. TSOP-5	Pin No. WDFNW6	Pin Name	Description
1	6	IN	Power supply input pin.
2	3	GND	Ground pin.
5	1	OUT	LDO output pin.
3	4	EN	Enable input pin (high – enabled, low – disabled). If this pin is connected to IN pin or if it is left unconnected (pull-up resistor is not required) the device is enabled.
4 (Note 1)	2	ADJ	Adjust input pin. Connect it to the output resistor divider or directly to the OUT pin.
4 (Note 1)	5	PG	Power good output pin. Could be left unconnected or could be connected to GND if not needed. High level for power ok, low level for fail.
4 (Note 1)	2, 5	NC	Not internally connected. This pin can be tied to the ground plane to improve thermal dissipation.
NA	EP	EPAD	Connect the exposed pad to GND.

#### PIN DESCRIPTION

1. Pin function depends on device version.

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
VIN Voltage (Note 2)	V <sub>IN</sub>	-0.3 to 22	V
VOUT Voltage	V <sub>OUT</sub>	–0.3 to [(V <sub>IN</sub> + 0.3) or 22 V; whichever is lower]	V
EN Voltage	V <sub>EN</sub>	–0.3 to (V <sub>IN</sub> + 0.3)	V
ADJ Voltage	V <sub>FB/ADJ</sub>	-0.3 to 5.5	V
PG Voltage	V <sub>PG</sub>	–0.3 to (V <sub>IN</sub> + 0.3)	V
Output Current	I <sub>OUT</sub>	Internally limited	mA
PG Current	I <sub>PG</sub>	3	mA
Maximum Junction Temperature	T <sub>J(MAX)</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	–55 to 150	°C
ESD Capability, Human Body Model (Note 3)	ESD <sub>HBM</sub>	2000	V
ESD Capability, Charged Device Model (Note 3)	ESD <sub>CDM</sub>	1000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

 This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per ANSI/ESDA/JEDEC JS-001, EIA/JESD22-A114 (AEC-Q100-002) ESD Charged Device Model tested per ANSI/ESDA/JEDEC JS-002, EIA/JESD22-C101 (AEC-Q100-011D)

#### THERMAL CHARACTERISTICS (Note 4)

Characteristic	Symbol	WDFNW6 2x2	TSOP-5	Unit
Thermal Resistance, Junction-to-Air	R <sub>thJA</sub>	63	147	°C/W
Thermal Resistance, Junction-to-Case (top)	R <sub>thJCt</sub>	204	82	°C/W
Thermal Resistance, Junction-to-Case (bottom)	R <sub>thJCb</sub>	15	N/A	°C/W
Thermal Resistance, Junction-to-Board (top)		47	113	°C/W
Thermal Characterization Parameter, Junction-to-Case (top)	Psi <sub>JCt</sub>	4	22	°C/W
Thermal Characterization Parameter, Junction-to-Board [FEM]	Psi <sub>JB</sub>	46	113	°C/W

Measured according to JEDEC board specification (board 1S2P, Cu layer thickness 1 oz, Cu area 650 mm<sup>2</sup>, no airflow). Detailed description
of the board can be found in JESD51–7.

# **ELECTRICAL CHARACTERISTICS** (V<sub>IN</sub> = V<sub>OUT-NOM</sub> + 1 V and V<sub>IN</sub> $\ge$ 2.7 V, V<sub>EN</sub> = 1.2 V, I<sub>OUT</sub> = 1 mA, C<sub>IN</sub> = C<sub>OUT</sub> = 1.0 $\mu$ F (effective capacitance – Note 5), T<sub>J</sub> = -40°C to 125°C, ADJ tied to OUT, unless otherwise specified) (Note 6)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Recommended Input Voltage		V <sub>IN</sub>	2.7	-	18	V
Output Voltage Accuracy	$T_J = -40^{\circ}C$ to $+85^{\circ}C$	V <sub>OUT</sub>	-1	-	1	%
	$T_{J} = -40^{\circ}C \text{ to } +125^{\circ}C$		-1	-	2	
ADJ Reference Voltage	ADJ version only	V <sub>ADJ</sub>	-	1.2	-	V
ADJ Input Current	V <sub>ADJ</sub> = 1.2 V	I <sub>ADJ</sub>	-0.1	0.01	0.1	μΑ
Line Regulation	$V_{IN}$ = $V_{OUT-NOM}$ + 1 V to 18 V and $V_{IN}$ $\geq$ 2.7 V	$\Delta V_{O(\Delta VI)}$	-	-	0.2	%V <sub>OUT</sub>
Load Regulation	I <sub>OUT</sub> = 0.1 mA to 100 mA	$\Delta V_{O(\Delta IO)}$	-	-	0.4	%V <sub>OUT</sub>
Quiescent Current (version A)	$V_{IN} = V_{OUT-NOM} + 1 V$ to 18 V, $I_{OUT} = 0 mA$	ا <sub>Q</sub>	-	1.3	2.5	μA
Quiescent Current (version B)	$V_{IN} = V_{OUT-NOM} + 1 V$ to 18 V, $I_{OUT} = 0 mA$		-	1.8	3.0	
Ground Current	I <sub>OUT</sub> = 100 mA	I <sub>GND</sub>	-	325	450	μA
Shutdown Current (Note 10)	$V_{EN} = 0 \text{ V}, \text{ I}_{OUT} = 0 \text{ mA}, \text{ V}_{IN} = 18 \text{ V}$	I <sub>SHDN</sub>	-	0.35	1.5	μA
Output Current Limit	$V_{OUT} = V_{OUT-NOM} - 100 \text{ mV}$	I <sub>OLIM</sub>	140	250	450	mA
Short Circuit Current	V <sub>OUT</sub> = 0 V	I <sub>OSC</sub>	140	250	450	mA
Dropout Voltage (Note 7)	I <sub>OUT</sub> = 100 mA	V <sub>DO</sub>	-	215	355	mV

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Power Supply Ripple Rejection	V <sub>IN</sub> = V <sub>OUT-NOM</sub> + 2 V	10 Hz	PSRR	_	80	-	dB
	I <sub>OUT</sub> = 10 mA	10 kHz		_	70	-	
		100 kHz		_	42	-	
		1 MHz		-	48	-	
Output Noise	f = 10 Hz to 100 kHz, $V_{OUT-N}$	<sub>OM</sub> = 5.0 V	V <sub>N</sub>	-	240	-	$\mu V_{\text{RMS}}$
EN Threshold	V <sub>EN</sub> rising		V <sub>EN-TH</sub>	0.7	0.9	1.05	V
EN Hysteresis	V <sub>EN</sub> falling		V <sub>EN-HY</sub>	0.01	0.1	0.2	V
EN Internal Pull-up Current	V <sub>EN</sub> = 1 V, V <sub>IN</sub> = 5.5 V		I <sub>EN-PU</sub>	0.01	0.3	1	μA
EN Input Leakage Current	V <sub>EN</sub> = 18 V, V <sub>IN</sub> = 18 V		I <sub>EN-LK</sub>	-1	0.05	1	μA
Start-up time (Note 8)	$V_{OUT-NOM} \le 3.3 V$		t <sub>START</sub>	100	250	500	μs
	V <sub>OUT-NOM</sub> > 3.3 V			300	600	1000	
Internal UVLO Threshold	Ramp $V_{IN}$ up until output is turned on		V <sub>IUL-TH</sub>	1.6	1.95	2.6	V
Internal UVLO Hysteresis	Ramp $V_{IN}$ down until output is turned off		V <sub>IUL-HY</sub>	0.05	0.2	0.3	V
PG Threshold (Note 9)	V <sub>OUT</sub> falling		V <sub>PG-TH</sub>	90	93	96	%
PG Hysteresis (Note 9)	V <sub>OUT</sub> rising		V <sub>PG-HY</sub>	0.1	2	4	%
PG Deglitch Time (Note 9)			t <sub>PG-DG</sub>	75	160	270	μs
PG Delay Time (Note 9)			t <sub>PG-DLY</sub>	120	320	600	μs
PG Output Low Level Voltage (Note 9)	I <sub>PG</sub> = 1 mA		V <sub>PG-OL</sub>	-	0.2	0.4	V
PG Output Leakage Current (Note 9)	V <sub>PG</sub> = 18 V		I <sub>PG-LK</sub>	-	0.01	1	μA
Thermal Shutdown Temperature	Temperature rising from $T_J = +25^{\circ}C$		T <sub>SD</sub>	-	165	-	°C
Thermal Shutdown Hysteresis	Temperature falling from T <sub>SD</sub>		T <sub>SDH</sub>	-	20	-	°C

<b>ELECTRICAL CHARACTERISTICS</b> (VIN = V <sub>OUT-NOM</sub> + 1 V and VIN $\ge$ 2.7 V, V <sub>EN</sub> = 1.2 V, I <sub>OUT</sub> = 1 mA, CIN = C <sub>OUT</sub> = 1.0 $\mu$ F
(effective capacitance – Note 5), $T_J = -40^{\circ}$ C to 125°C, ADJ tied to OUT, unless otherwise specified) (Note 6) (continued)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Effective capacitance, including the effect of DC bias, tolerance and temperature. See the Application Information section for more information.

 Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.

7. Dropout measured when the output voltage falls 100 mV below the nominal output voltage. Limits are valid for all voltage versions.

8. Startup time is the time from EN assertion to point when output voltage is equal to 95% of  $V_{OUT-NOM}$ .

9. Applicable only to version B (device option with power good output). PG threshold and PG hysteresis are expressed in percentage of nominal output voltage.

10. Shutdown current includes EN Internal Pull-up Current.

#### **TYPICAL CHARACTERISTICS**

 $V_{IN} = V_{OUT-NOM} + 1 V \text{ and } V_{IN} \ge 2.7 V, V_{EN} = 1.2 V, I_{OUT} = 1 \text{ mA}, C_{OUT} = 1.0 \mu\text{F}, \text{ADJ tied to OUT}, T_J = 25^{\circ}\text{C}, \text{ unless otherwise specified}$ 



Figure 10. Enable Internal Pull-Up Current vs. Temperature

#### **TYPICAL CHARACTERISTICS**

 $V_{IN} = V_{OUT-NOM} + 1 \text{ V and } V_{IN} \geq 2.7 \text{ V}, V_{EN} = 1.2 \text{ V}, I_{OUT} = 1 \text{ mA}, C_{OUT} = 1.0 \text{ } \mu\text{F}, \text{ ADJ tied to OUT}, T_J = 25^{\circ}\text{C}, \text{ unless otherwise specified}$ 



Figure 12. Dropout Voltage vs. Temperature

#### **TYPICAL CHARACTERISTICS**

 $V_{IN} = V_{OUT-NOM} + 1 V \text{ and } V_{IN} \ge 2.7 V, V_{EN} = 1.2 V, I_{OUT} = 1 \text{ mA}, C_{OUT} = 1.0 \mu\text{F}, \text{ADJ tied to OUT}, T_J = 25^{\circ}\text{C}, \text{ unless otherwise specified}$ 



Figure 13. PSRR – FIX–3.3 V, C<sub>OUT</sub> = 1  $\mu$ F, I<sub>OUT</sub> = 100 mA



Figure 15. PSRR – FIX–3.3 V,  $V_{IN}$  = 8.3 V,  $I_{OUT}$  = 100 mA



Figure 14. PSRR – FIX–3.3 V, V<sub>IN</sub> = 4.3 V, I<sub>OUT</sub> = 100 mA



Figure 16. Noise – FIX – 5.0 V,  $I_{OUT}$  = 10 mA, Different C<sub>OUT</sub>



#### **ORDERING INFORMATION**

Part Number	Marking	Voltage Option (V <sub>OUT-NOM</sub> )	Version	Package	Shipping	
NCV8711ASNADJT1G	GGA	ADJ				
NCV8711ASN300T1G	GGC	3.0 V	Without PG TSOP-5 (Pb-Free)		3000 / Tape & Reel	
NCV8711ASN330T1G	GGD	3.3 V				
NCV8711ASN500T1G	GGE	5.0 V				
NCV8711BMTWADJTBG	GA	ADJ				
NCV8711BMTW300TBG	GC	3.0 V		WDFNW6	0000 / Tana & Daal	
NCV8711BMTW330TBG	GD	3.3 V	wiiii PG	(Pb-Free)	SUUU / Tape & Reel	
NCV8711BMTW500TBG	GE	5.0 V				

NOTE: To order other package, voltage version or PG / non PG variant, please contact your ON Semiconductor sales representative.





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